GM	10	W
pp		

j

$_j$=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
I_{GT}					
GT					
	V_D=V_{DRM} =3.3kΩ	0.2V			
I	I I=1.2 $_{GT}$-40				mA
	0.4V Ope				
tonl	A=200mA 20mA				
toff	T $_j$=25				

V	I =±23A $_p$380	=21.6V	
	$_{TO}$Threshold voltage	=1025 7V	
R_D		=1296Ω	
DRM	V_D=V_{DRM} V_R=V_{RM}	T=25	
RRM T			

Symbol Parameter	Value	Unit
R junction to case (DC)	4.5	/W

Symbol Parameter Value(MAX) Unit

FIG.1: Maximum power dissipation versus RMS on-state current

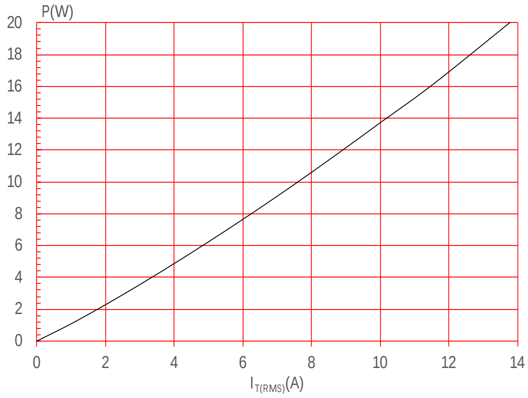


FIG.2: RMS on-state current versus case temperature

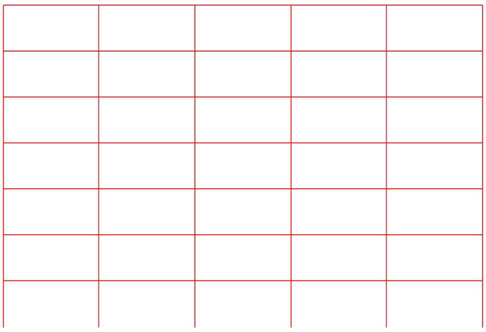


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

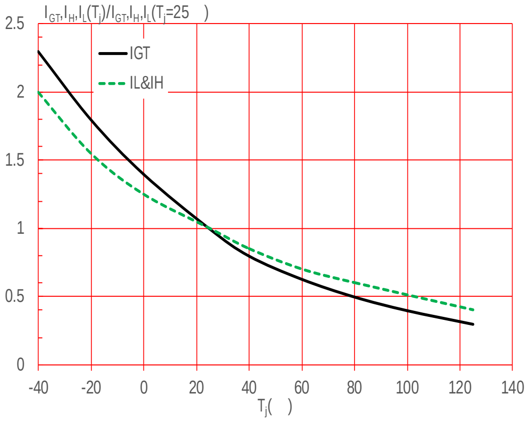
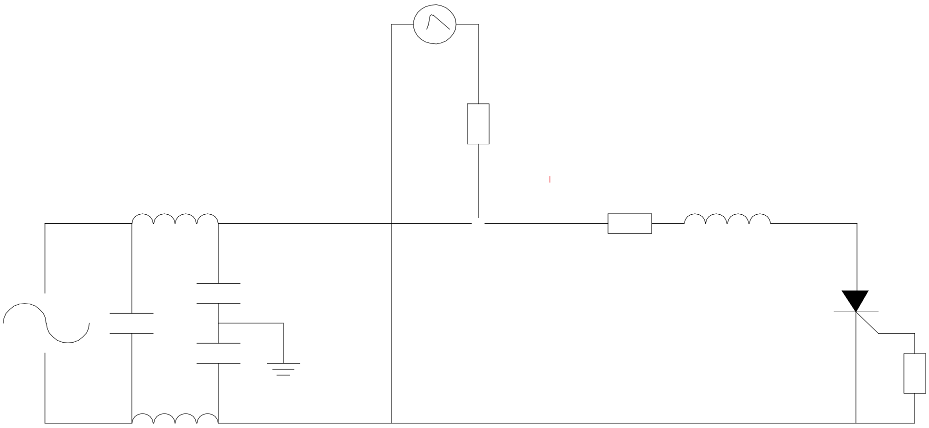
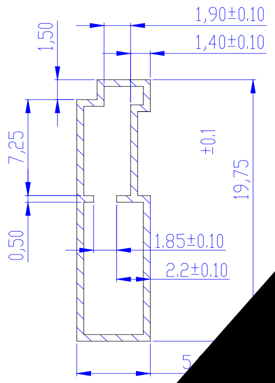


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
C	0.40		0.60	0.016		0.024
D	5.90		6.30	0.232		0.248
E	6.40		6.80	0.252		0.268
				0.053		0.65
G	4.47					
G1	2.18		2.38	0.086		0.094
L						
L2				0.053		0.065



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